Memory FRAM

256 K (32 K \times 8) Bit

MB85R256F

DESCRIPTIONS

The MB85R256F is an FRAM (Ferroelectric Random Access Memory) chip in a configuration of 32,768 words \times 8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells.

The MB85R256F is able to retain data without using a back-up battery, as is needed for SRAM.

The memory cells used in the MB85R256F can be used for 10¹² read/write operations, which is a significant improvement over the number of read and write operations supported by Flash memory and E²PROM.

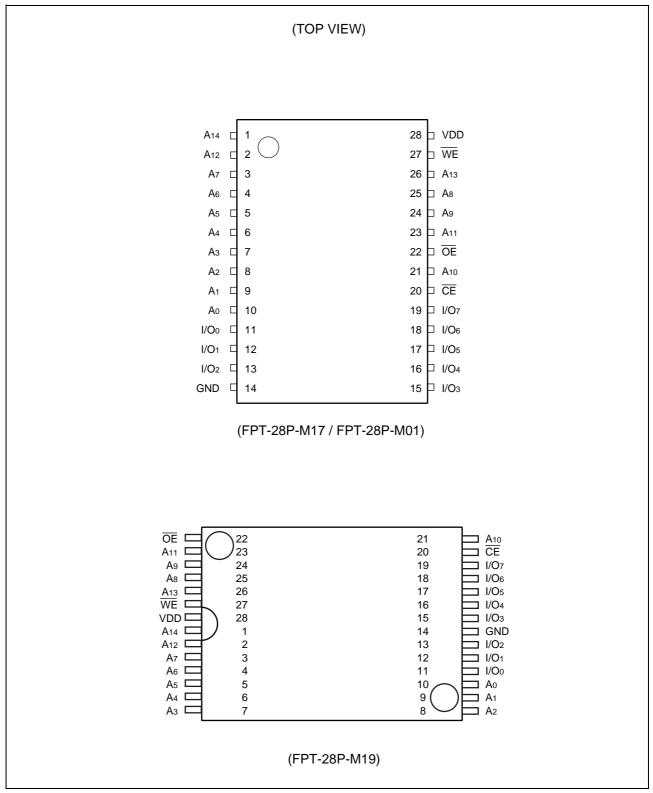
The MB85R256F uses a pseudo - SRAM interface compatible with conventional asynchronous SRAM.

FEATURES

- Bit configuration : 32,768 words × 8 bits
- Read/write endurance : 10¹² times / byte
- Data retention : 10 years (+85 °C), 95 years (+55 °C), over 200 years (+35 °C)
- Operating power supply voltage : 2.7 V to 3.6 V
- Low power consumption : Operating power supply current 5 mA (Typ)
- Standby current 5 µA (Typ)
- Operation ambient temperature range: 40 $^{\circ}\text{C}$ to $\,+$ 85 $^{\circ}\text{C}$
- Package
- : 28-pin plastic SOP (FPT-28P-M17) 28-pin plastic SOP (FPT-28P-M01)
- : 28-pin plastic TSOP(1) (FPT-28P-M19)
 - Both are RoHS compliant



■ PIN ASSIGNMENTS

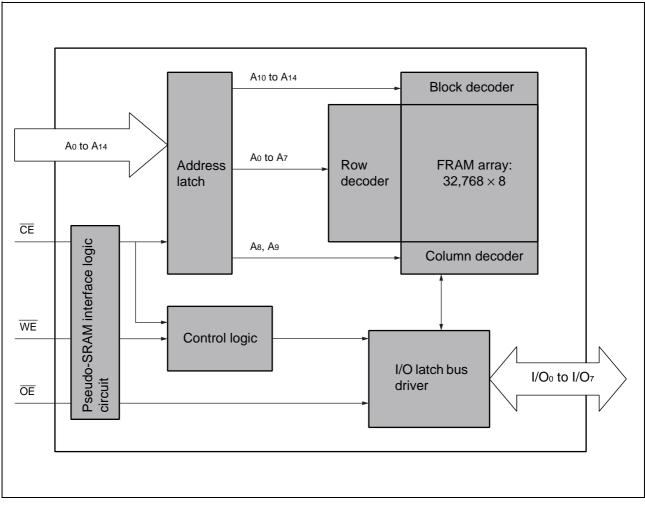


| Pin no. | Pin name | Functional description |
|-----------------------|--------------------------------------|-------------------------|
| 1 to 10, 21, 23 to 26 | A ₀ to A ₁₄ | Address input pins |
| 11 to 13, 15 to 19 | I/O ₀ to I/O ₇ | Data input/output pins |
| 20 | CE | Chip enable input pin |
| 27 | WE | Write Enable input pin |
| 22 | ŌĒ | Output enable input pin |
| 28 | VDD | Supply Voltage pin |
| 14 | GND | Ground pin |

■ PIN FUNCTIONAL DESCRIPTIONS



BLOCK DIAGRAM



■ FUNCTION LIST

| Operation mode | CE | WE | ŌĒ | I/O ₀ to I/O ₇ | Power supply current |
|-------------------|----|----|------------|--------------------------------------|----------------------|
| | Н | × | × | | 0, " |
| Standby precharge | × | L | L | Hi-Z | Standby (Isв) |
| | × | Н | Н | | (102) |
| | L | ۲ | ٦ <u>۲</u> | | |
| Latch address | Ţ | Н | L | — | — |
| | Ţ | L | Н | | |
| Write | L | L | Н | Data input | Operation (IDD) |
| Read | L | Н | L | Data output | |

H: High level, L: Low level, \times : can be either H, L, \neg or \neg , Hi-Z: High impedance, \neg : Latch address at falling edge

■ ABSOLUTE MAXIMUM RANGES

| Parameter | Symbol | Rat | Unit | |
|-------------------------------|--------|-------|-----------|------|
| Falameter | Symbol | Min | Max | Unit |
| Power supply voltage* | Vdd | - 0.5 | + 4.0 | V |
| Input voltage* | VIN | - 0.5 | Vdd + 0.5 | V |
| Output voltage* | Vout | - 0.5 | Vdd + 0.5 | V |
| Operation ambient temperature | TA | - 40 | + 85 | °C |
| Storage temperature | Tstg | - 55 | + 125 | °C |

* : These parameters are based on the condition that Vss is 0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

| Parameter | Symbol | | Unit | | |
|-------------------------------|--------|--------------------|------|-----------|------|
| Falameter | Symbol | Min | Тур | Max | Unit |
| Power supply voltage* | Vdd | 2.7 | 3.3 | 3.6 | V |
| High level input voltage* | Vін | $V_{DD} 	imes 0.8$ | — | Vdd + 0.5 | V |
| Low level input voltage* | VIL | - 0.5 | | + 0.6 | V |
| Operation ambient temperature | TA | - 40 | | + 85 | °C |

*: These parameters are based on the condition that Vss is 0 V.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(within recommended operating conditions)

| · · · · | | | | | | |
|-------------------------------------|--------|--|----------------------------|-----|------|------|
| Parameter | Symbol | Conditions | | | Unit | |
| Farameter | Symbol | Conditions | Min | Тур | Max | Unit |
| Input leakage current | u | $V_{IN} = 0 V \text{ to } V_{DD}$ | — | | 10 | μΑ |
| Output leakage current | Ilo | | _ | | 10 | μA |
| Operating power supply current*1 | lod | $\label{eq:cell} \begin{split} \overline{CE} &= 0.2 \text{ V},\\ \text{Other inputs} &= V_{\text{DD}} - 0.2 \text{ V}/0.2 \text{ V},\\ t_{\text{RC}} (\text{Min}), \text{ lout} &= 0 \text{ mA} \end{split}$ | | 5 | 10 | mA |
| Standby current*2 | lsв | $\overline{CE}, \overline{WE}, \overline{OE} \ge V_{DD}$ | — | 5 | 50 | μA |
| High level output voltage | Vон | Iон = - 2.0 mA | $V_{\text{DD}} \times 0.8$ | | | V |
| Low level output voltage | Vol | lo∟ = 2.0 mA | _ | | 0.4 | V |

*1: During the measurement of IDD, the Address and Data In were taken to only change once per active cycle. Iout: output current

*2: All pins other than setting pins shall be input at the CMOS level voltages such as $H \ge V_{DD}$, $L \le 0 V$.

2. AC Characteristics

• AC Characteristics Test Condition

Power supply voltage : 2.7 V to 3.6 V

Operation ambient temperature: $-40 \degree C$ to $+85 \degree C$

Input voltage amplitude : 0.3 V to 2.7 V

| Input rising time | : 10 ns |
|-------------------|---------|
| | |

Input falling time : 10 ns

Input evaluation level : VDD/2

Output evaluation level : VDD/2

Output Load Capacitance: 100 pF

(1) Read cycle

| Parameter | Symbol | Va | lue | Unit |
|-------------------------|-------------|-----|-----|------|
| Falameter | Symbol | Min | Max | Onit |
| Read cycle time | trc | 150 | | |
| CE active time | t CA | 70 | 500 | |
| Read pulse width | t RP | 70 | 500 | |
| Precharge time | t PC | 80 | — | |
| Address setup time | tas | 0 | | 20 |
| Address hold time | tан | 25 | — | ns |
| CE access time | tce | — | 70 | |
| OE access time | toe | — | 70 | |
| CE output floating time | tнz | | 25 | |
| OE output floating time | tонz | | 25 | |



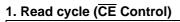
(2) Write cycle

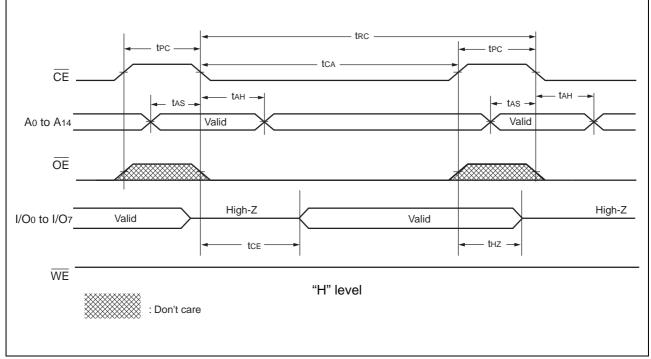
| Parameter | Symbol | Va | lue | Unit |
|--------------------|-------------|-----|-----|------|
| Faiametei | Symbol | Min | Мах | Unit |
| Write cycle time | twc | 150 | — | |
| CE active time | t CA | 70 | 500 | |
| Write pulse width | twp | 70 | 500 | |
| Precharge time | t PC | 80 | — | ns |
| Address setup time | tas | 0 | | 115 |
| Address hold time | tан | 25 | | |
| Data setup time | tos | 50 | — | |
| Data hold time | tон | 0 | | |

3. Pin Capacitance

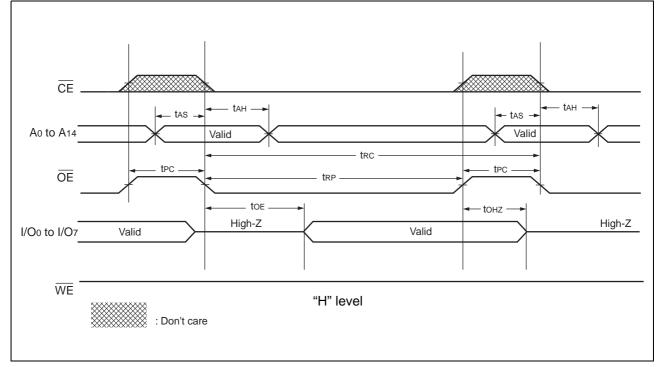
| Parameter | Symbol | Conditions | Conditions | | | Unit |
|--------------------|--------|---|------------|-----|-----|------|
| Farameter | Symbol | Conditions | Min | Тур | Max | Onit |
| Input capacitance | CIN | $V_{DD} = V_{IN} = V_{OUT} = 0 V,$ | | | 10 | pF |
| Output capacitance | Соит | $f = 1 \text{ MHz}, T_A = +25 ^{\circ}\text{C}$ | | | 10 | pF |

■ TIMING DIAGRAM



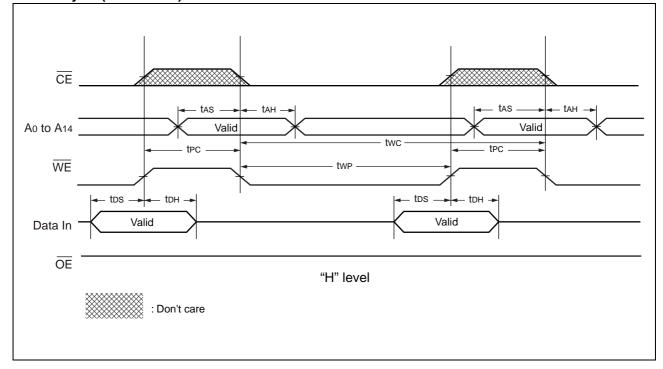


2. Read cycle (OE Control)

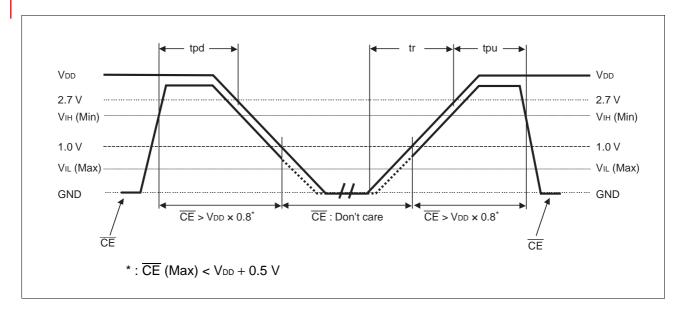


3. Write cycle (CE Control) - twc tPC -– tPC -– tca -CE _ tas _ 🛶 tah 🛶 – tas — 🗕 tah — A0 to A14 Valid Valid WE ************* _ tds ____ tdh -– tDS – — tDH 🗕 Valid Valid Data In ŌĒ "H" level : Don't care

4. Write cycle (WE Control)



■ POWER ON/OFF SEQUENCE



| Parameter | Symbol | | Unit | | |
|---------------------------------|--------|------|------|-----|------|
| Farameter | Symbol | Min | Тур | Max | Unit |
| CE level hold time at power OFF | tpd | 80 | _ | | ns |
| CE level hold time at power ON | tpu | 80 | _ | | ns |
| Power supply rising time | tr | 0.05 | | 200 | ms |

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

■ FRAM CHARACTERISTICS

| ltem | Min | Max | Unit | Parameter |
|------------------------|-------------------------|-----|------------|---|
| Read/Write Endurance*1 | 10 ¹² | _ | Times/byte | Operation Ambient Temperature $T_A = +85 \ ^{\circ}C$ |
| | 10 | _ | | Operation Ambient Temperature $T_A = +85 \ ^{\circ}C$ |
| Data Retention*2 | 95 | | Years | Operation Ambient Temperature $T_A = +55 \ ^{\circ}C$ |
| | ≥ 200 | _ | | Operation Ambient Temperature $T_A = +35 \ ^{\circ}C$ |

*1 : Total number of reading and writing defines the minimum value of endurance, as an FRAM memory operates with destructive readout mechanism.

*2 : Minimun values define retention time of the first reading/writing data right after shipment, and these values are calculated by qualification results.

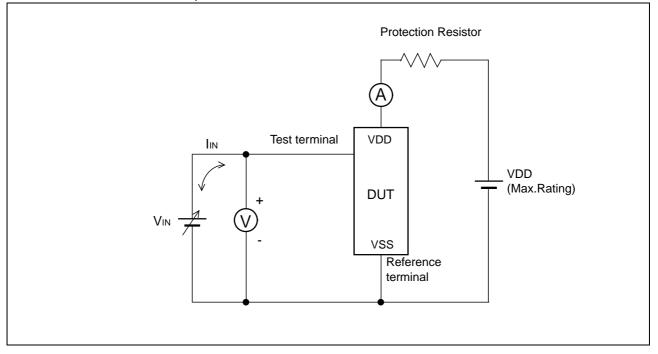
NOTES ON USE

After the IR reflow completed, it is not guaranteed to save the data written prior to the IR reflow.

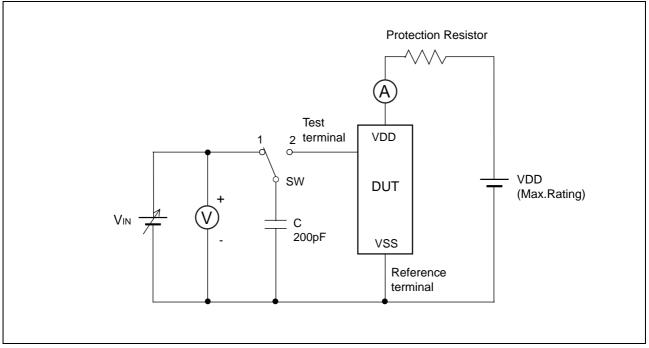
■ ESD AND LATCH-UP

| Test | DUT | Value |
|---|--|-----------|
| ESD HBM (Human Body Model) JESD22-A114 compliant | | ≥ 2000 V |
| ESD MM (Machine Model) JESD22-A115 compliant | | ≥ 200 V |
| ESD CDM (Charged Device Model) JESD22-C101 compliant | | ≥ 1000 V |
| Latch-Up (I-test) JESD78 compliant | MB85R256FPF-G-BNDE1 MB85R256FPFCN-G-BNDE1 | |
| Latch-Up (V _{supply} overvoltage test) JESD78 compliant | | |
| Latch-Up (Current Method) Proprietary method | | ≥ 300 mA |
| Latch-Up (C-V Method) Proprietary method | | _ |

• Current method of Latch-Up Resistance Test



Note : The voltage V_{IN} is increased gradually and the current I_{IN} of 300 mA at maximum shall flow. Confirm the latch up does not occur under I_{IN} = ± 300 mA. In case the specific requirement is specified for I/O and I_{IN} cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement. • C-V method of Latch-Up Resistance Test



Note : Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle.

Repeat this process 5 times. However, if the latch-up condition occurs before completing 5 times, this test must be stopped immediately.

ĪTSU

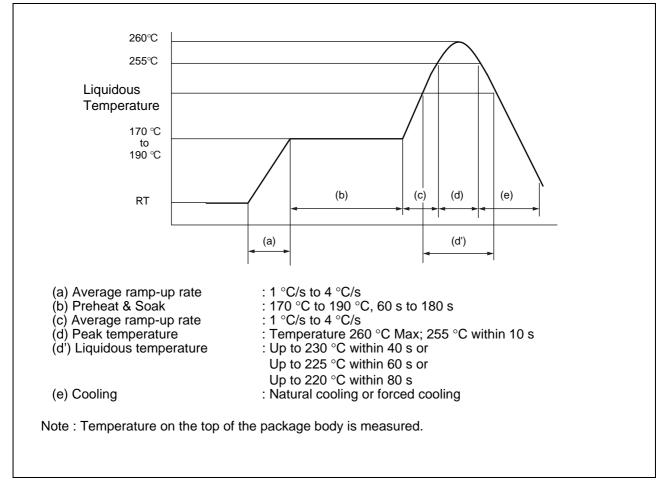
FL



■ REFLOW CONDITIONS AND FLOOR LIFE

| Item | Condition | | | | | | |
|----------------------|-----------------------------------|---|--|--|--|--|--|
| Method | IR (infrared reflow), Convection | | | | | | |
| Times | 2 | | | | | | |
| | Before unpacking | Please use within 2 years after production. | | | | | |
| | From unpacking to 2nd reflow | Within 8 days | | | | | |
| Floor life | In case over period of floor life | Baking with 125 °C+/-3 °C for 24hrs+2hrs/-0hrs is required. Then please use within 8 days. (Please remember baking is up to 2 times) | | | | | |
| Floor life condition | | Between 5 °C and 30 °C and also below 70%RH required. (It is preferred lower humidity in the required temp range.) | | | | | |

Reflow Profile



RESTRICTED SUBSTANCES

This product complies with the regulations below (Based on current knowledge as of November 2011).

- EU RoHS Directive (2002/95/EC)
- China RoHS (Administration on the Control of Pollution Caused by Electronic Information Products (电子信息产品污染控制管理办法))
- Vietnam RoHS (30/2011/TT-BCT)

Restricted substances in each regulation are as follows.

| Substances | Threshold | Contain status* |
|---------------------------------------|-----------|-----------------|
| Lead and its compounds | 1,000 ppm | О |
| Mercury and its compounds | 1,000 ppm | О |
| Cadmium and its compounds | 100 ppm | О |
| Hexavalent chromium compound | 1,000 ppm | О |
| Polybrominated biphenyls (PBB) | 1,000 ppm | О |
| Polybrominated diphenyl ethers (PBDE) | 1,000 ppm | О |

* : The mark of "O" shows below a threshold value.

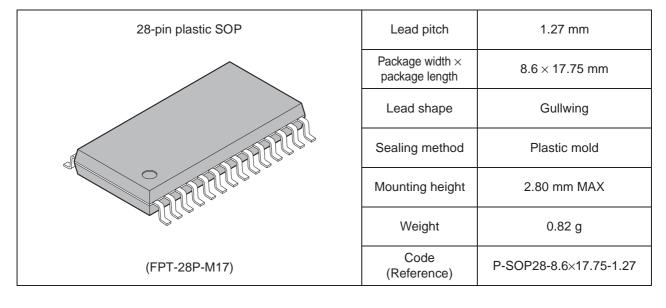


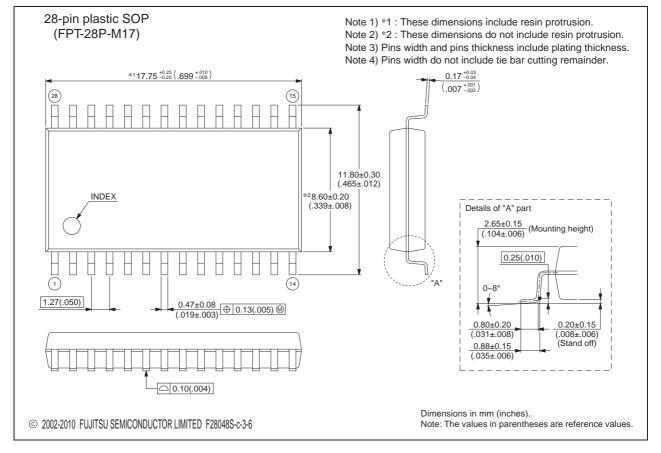
■ ORDERING INFORMATION

| Part number Package | | Shipping form | Minimum shipping quantity |
|------------------------|--|-----------------------|------------------------------|
| MB85R256FPF-G-BNDE1 | MB85R256FPF-G-BNDE128-pin plastic SOP (FPT-28P-M17)Tube | | 1 |
| MB85R256FPFCN-G-BNDE1 | 28-pin plastic TSOP(1) (FPT-28P-M19) | Tray | 1 |
| MB85R256FPF-G-BND-ERE1 | 28-pin plastic SOP (FPT-28P-M17) | Embossed carrier tape | 1000 |
| MB85R256FPNF-G-JNE2 | 28-pin plastic SOP (FPT-28P-M01) | Tube | 1 |
| MB85R256FPNF-G-JNERE2 | 28-pin plastic SOP (FPT-28P-M01) | Embossed carrier tape | 1000 |



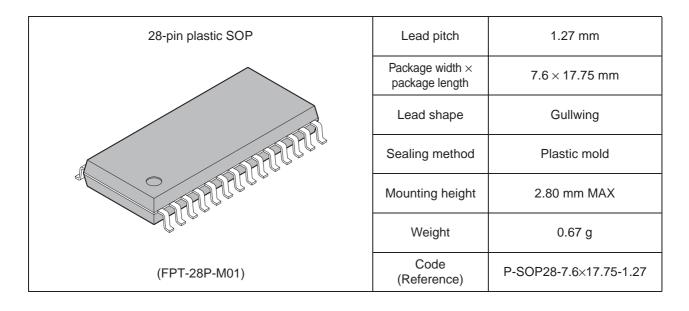
PACKAGE DIMENSIONS

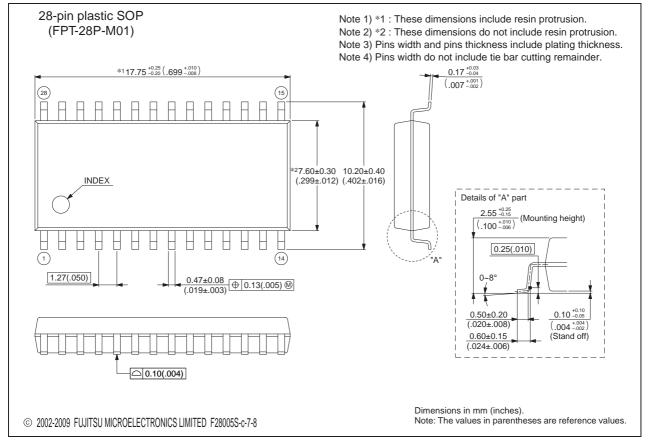




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ITSU

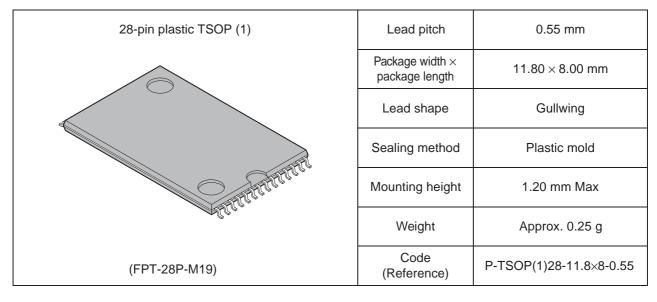


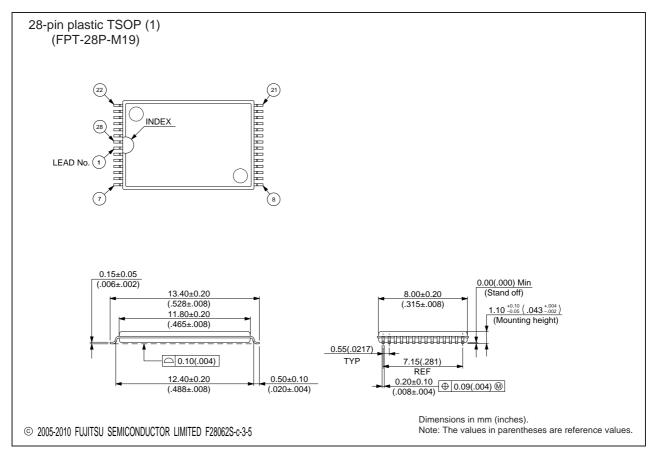


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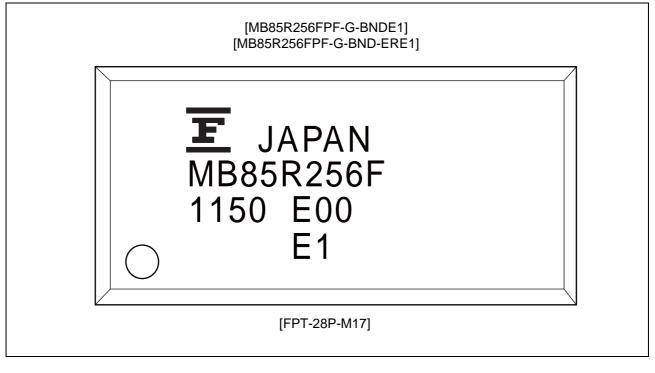
MB85R256F

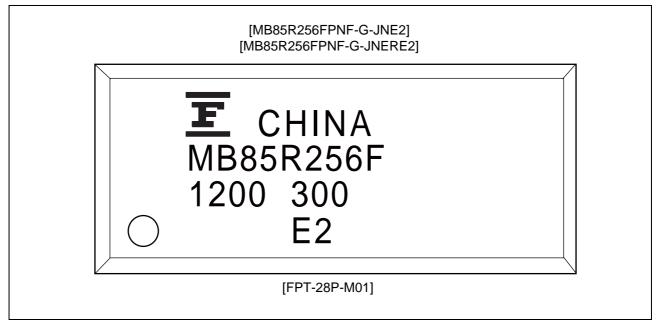
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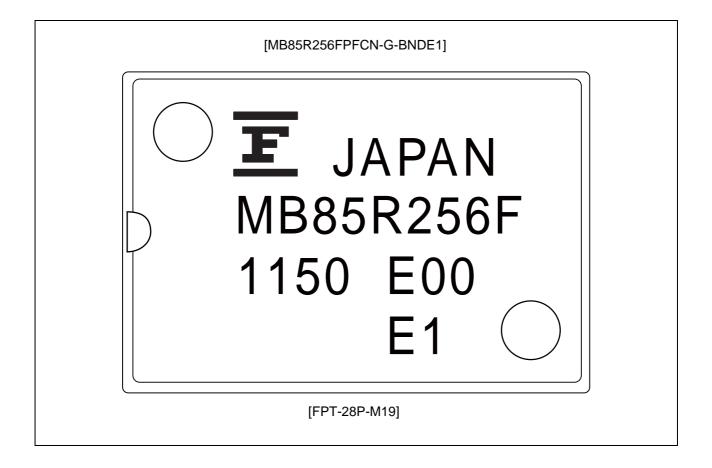




■ MARKING



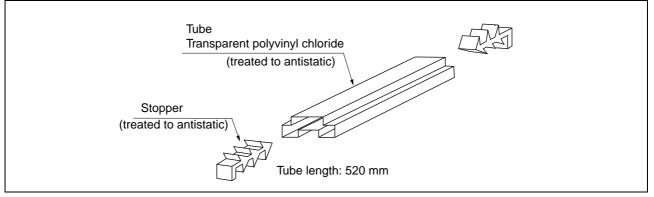




PACKING INFORMATION

1. Tube

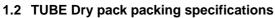
- 1.1 Tube Dimensions
 - Tube/stopper shape

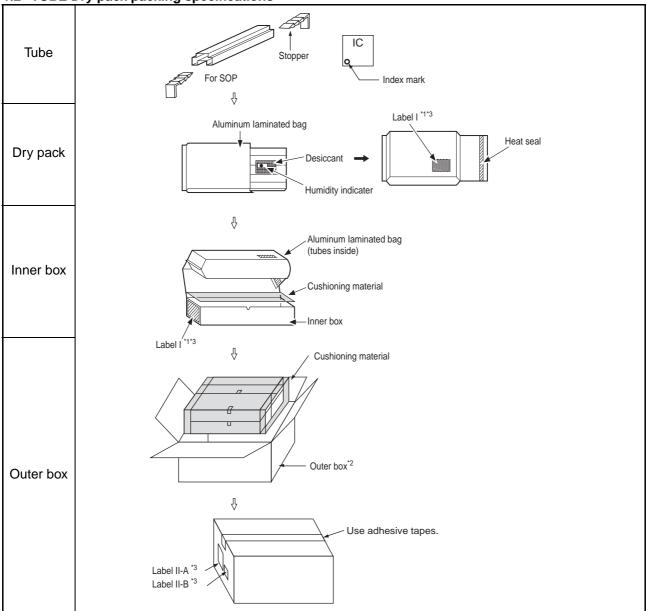


Tube cross-sections and Maximum quantity

| Backage form | Dookogo oodo | Maximum quantity | | | | |
|---|--------------|------------------|---------------|---------------|--|--|
| Package form | Package code | pcs/tube | pcs/inner box | pcs/outer box | | |
| SOP, 28, plastic | FPT-28P-M17 | 28 | 2240 | 8960 | | |
| (10.6) 9.4 9.4 ((6.8) (6.8) (14.4) (15.6) (6.8) (14.4) (15.6) (10.6) | | | | | | |
| Transparent polyvinyl chloride | | | | | | |

(Dimensions in mm)





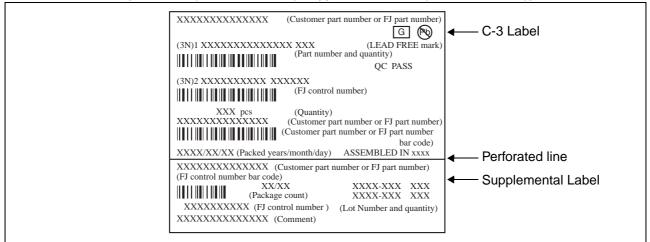
- *1: For a product of witch part number is suffixed with "E1", a " G (B) " marks is display to the moisture barrier bag and the inner boxes.
- *2: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

*3: Please refer to an attached sheet about the indication label.

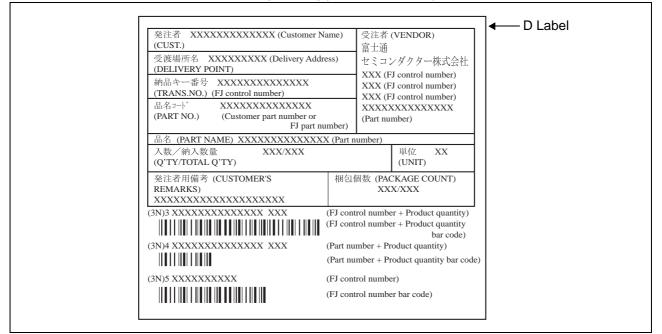
Note: The packing specifications may not be applied when the product is delivered via a distributer.

1.3 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



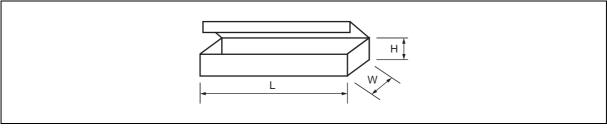
Label II-B: Outer boxes product indicate

| XXXXXXXXXXXXXXXX | (Part number) | | |
|--------------------------------------|--------------------------|---------------------------------------|--|
| (Lot Number) XXXX-XXX XXXX-XXX | (Count) X箱 X箱 計 | (Quantity) XXX 個 XXX 個 XXX 個 | |

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

1.4 Dimensions for Containers

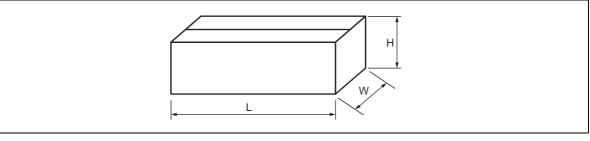
(1) Dimensions for inner box



| L | W | Н |
|-----|-----|----|
| 540 | 125 | 75 |
| | | |

(Dimensions in mm)

(2) Dimensions for outer box

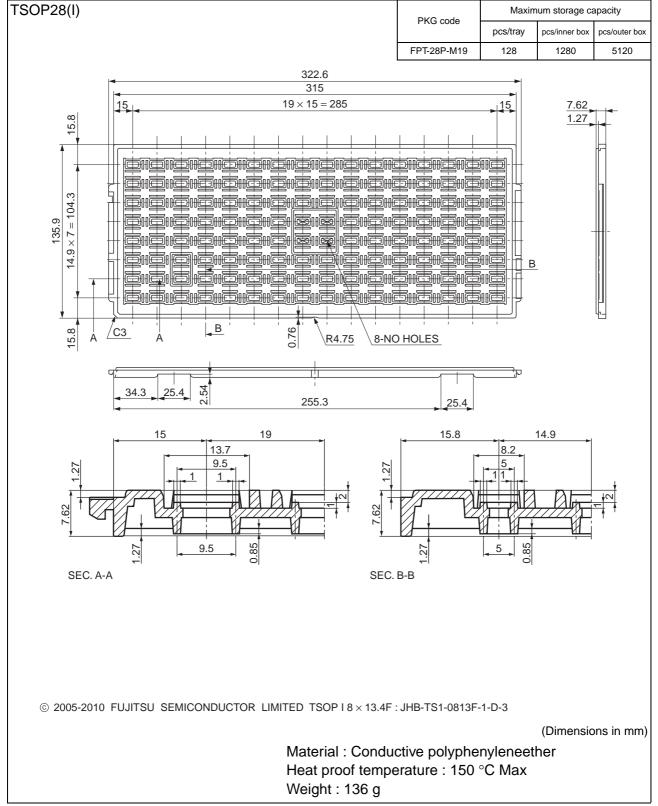


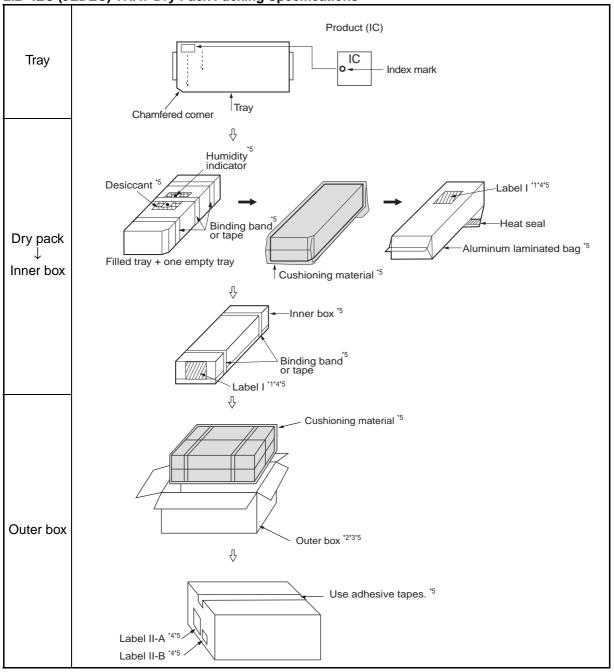
| L | W | Н |
|-----|-----|-----|
| 565 | 270 | 180 |

(Dimensions in mm)

2. Tray

2.1 Tray Dimensions





2.2 IEC (JEDEC) TRAY Dry Pack Packing Specifications

- *1: For a product of witch part number is suffixed with "E1", a " G (B) " marks is display to the moisture barrier bag and the inner boxes.
- *2: The size of the outer box may be changed depending on the quantity of inner boxes.
- *3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.
- *4: Please refer to an attached sheet about the indication label.
- *5: The packing materials except tray may differ slightly from the color and dimensions depend on country of manufacture.
- Note: The packing specifications may not be applied when the product is delivered via a distributer.

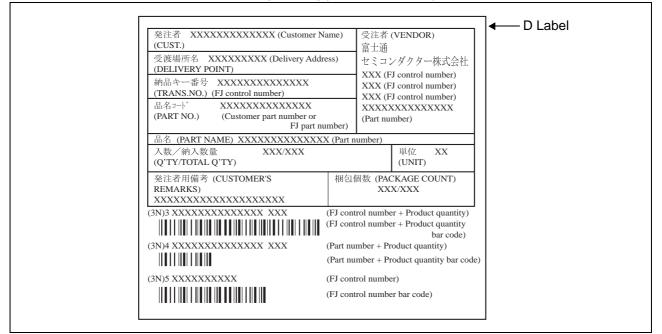


2.3 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]

| XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX | ← C-3 Label |
|--|--------------------|
| (3N)1 XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX | |
| (3N)2 XXXXXXXX XXXXXXXXXXXXXXXXXXXXXXXXXXX | |
| XXX pcs (Quantity) XXXXXXXXXXXXXXX (Customer part number or FJ part number) | |
| bar code) XXXX/XX/XX (Packed years/month/day) ASSEMBLED IN xxxx XXXXXXXXXXXXXXX (Customer part number or FJ part number) | Perforated line |
| (FJ control number bar code) XX/XX XXXX-XXX XXX (Package count) XXX-XXX XXX | Supplemental Label |
| XXXXXXXXX (FJ control number) (Lot Number and quantity) XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX | |

Label II-A: Label on Outer box [D Label] (100mm × 100mm)



Label II-B: Outer boxes product indicate

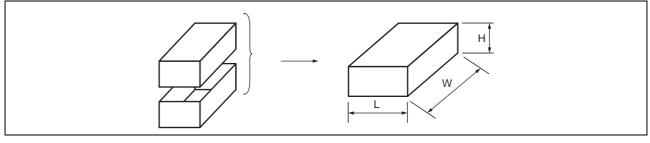
| XXXXXXXXXXXXXXXX | (Part number) | | |
|--------------------------------------|--------------------------|---------------------------------------|--|
| (Lot Number) XXXX-XXX XXXX-XXX | (Count) X箱 X箱 計 | (Quantity) XXX 個 XXX 個 XXX 個 | |

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

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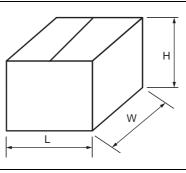
2.4 Dimensions for Containers

(1) Dimensions for inner box



| L | W | Н |
|-----|-----|--------------------|
| 165 | 360 | 75 |
| | | (Dimensions in mm) |

(2) Dimensions for outer box

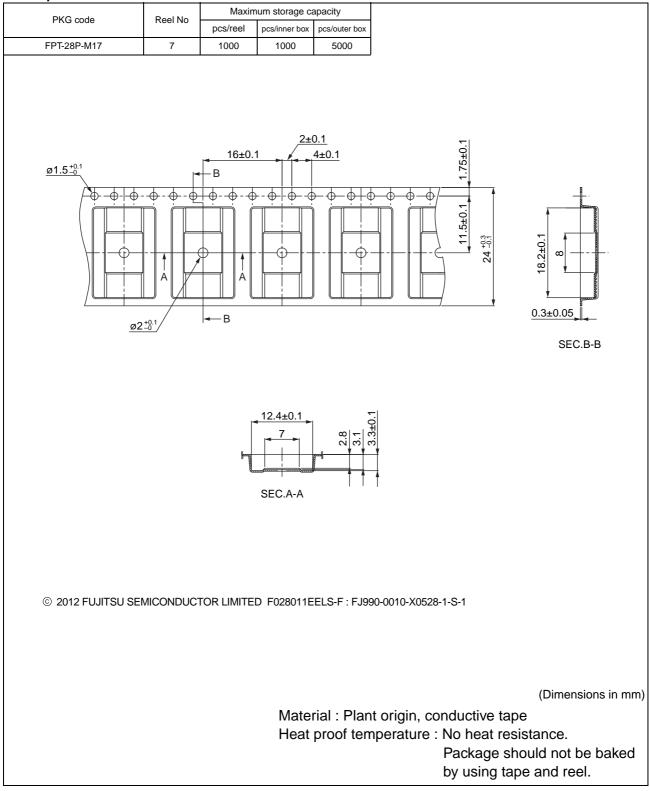


| 355 385 195 | L | W | Н |
|-------------|---|-----|-----|
| | | 385 | 195 |

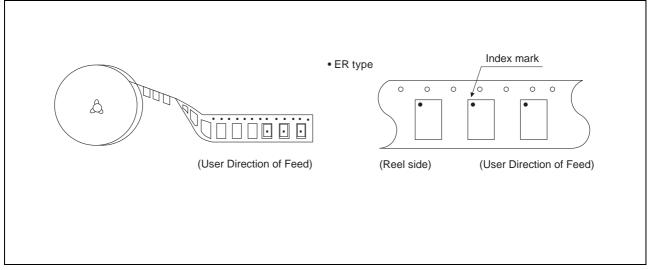
(Dimensions in mm)

3. Tape

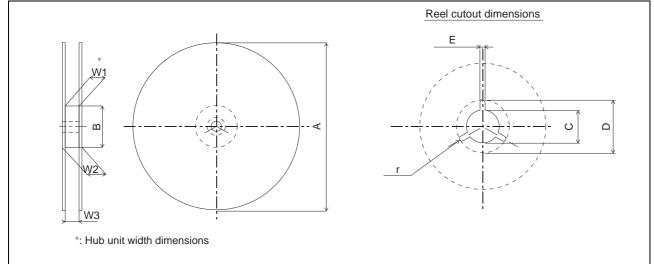
3.1 Tape Dimensions



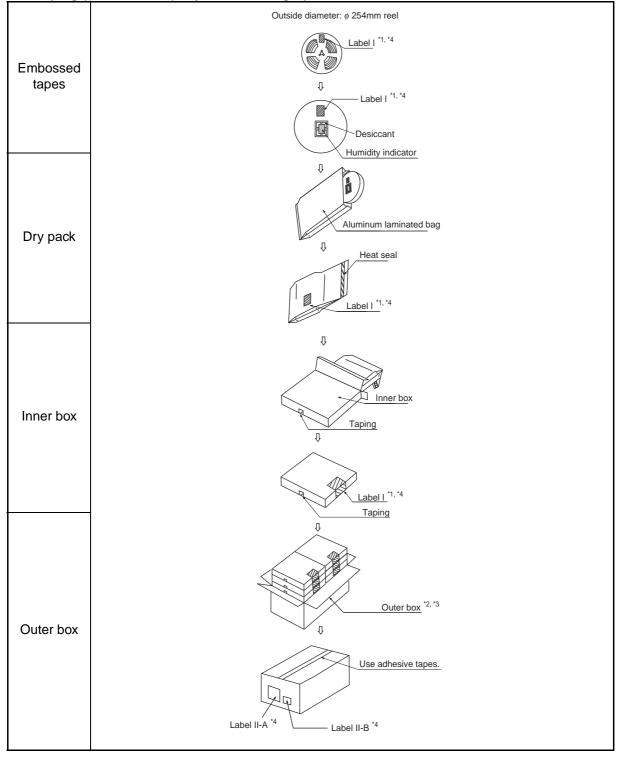
3.2 IC orientation



3.3 Reel dimensions



| | | | | | | _ | | | | | | | D | imensior | ns in mm |
|----------------------|-------------------|--|---------|----------|---------|-----------|---------|--|---|-------------------|-------------------|----------------|----------------|----------------|----------|
| Reel No | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | 13 | 14 | 15 |
| Tape width Symbol | 8 | | | | | | | | | 12 | 16 | 24 | | | |
| A | 254 ± 2 | 254 ± 2 254 ± 2 330 ± 2 254 ± 2 330 ± 2 254 ± 2 330 ± 2 330 ± 2 330 ± 2 | | | | | | | | | | | | | |
| В | | 100 ⁺² ₋₀ 100 ⁺² ₋₀ 150 ⁺² ₋₀ 100 ⁺² ₋₀ 100 ⁺² ₋₀ 100 ⁺² ₋₀ | | | | | | | | | 100 ± 2 | | | | |
| С | | 13 ± 0.2 $13^{+0.5}_{-0.2}$ | | | | | | | | | | | | | |
| D | | 21 ± 0.8 20.5 ⁺¹ _{-0.2} | | | | | | | | | | | | | |
| E | | | | | | | | 2 ± 0.5 | | | | | | | |
| W1 | 8.4 +2 | $8.4_{.0}^{+2} \qquad 12.4_{.0}^{+2} \qquad 16.4_{.0}^{+2} \qquad 24.4_{.0}^{+2} \qquad 32.4_{.0}^{+2} \qquad 44.4_{.0}^{+2} \qquad 56.4_{.0}^{+2} \qquad 12.4_{.0}^{+1} \qquad 16.4_{.0}^{+1} \qquad 16.4_$ | | | | | | | | 24.4+0.1 | | | | | |
| W2 | less than 14.4 | less that | an 18.4 | less the | an 22.4 | less that | an 30.4 | less than 38.4 less than 50.4 less than 62.4 | | less than 62.4 | less than 18.4 | less than 22.4 | less than 30.4 | | |
| W3 | 7.9 ~ 10.9 | 11.9 - | ~ 15.4 | 15.9 | ~ 19.4 | 23.9 - | ~ 27.4 | .4 31.9 ~ 35.4 43.9 ~ 47.4 55.9 ~ 59.4 | | | | 12.4 ~ 14.4 | 16.4 ~ 18.4 | 24.4 ~ 26.4 | |
| r | | | | 1 | | 1 | | 1.0 | | | | 1 | 1 | 1 | 1 |



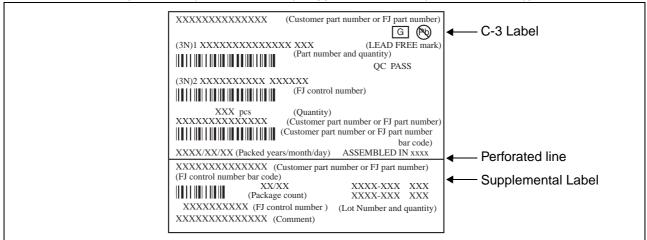
3.4 Taping (\u03e9330mm Reel) Dry Pack Packing Specifications

- *1: For a product of witch part number is suffixed with "E1", a " G ()" marks is display to the moisture barrier bag and the inner boxes.
- *2: The size of the outer box may be changed depending on the quantity of inner boxes.
- *3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.
- *4: Please refer to an attached sheet about the indication label.
- Note: The packing specifications may not be applied when the product is delivered via a distributer.

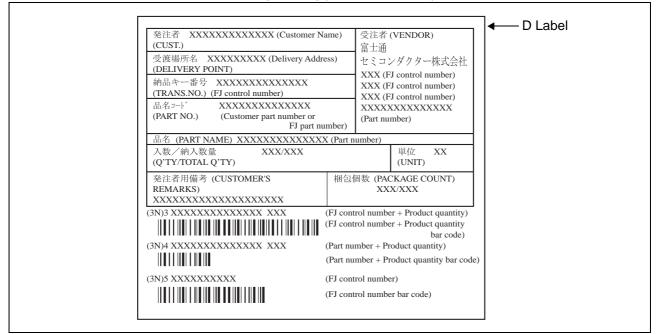


3.5 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



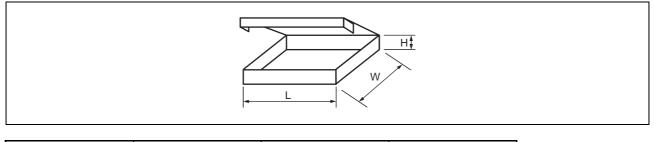
Label II-B: Outer boxes product indicate

| xxxxxxxxxx | XXX (Part number) | | |
|------------------------------------|-------------------|---------------------------------------|--|
| (Lot Numbe XXXX-XXX XXXX-XXX | X 箱 X 箱 | (Quantity) XXX 個 XXX 個 XXX 個 | |

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

3.6 Dimensions for Containers

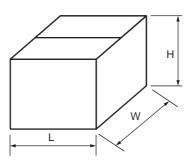
(1) Dimensions for inner box



| Tape width | L | W | Н |
|------------|-----|-----|----|
| 12, 16 | 365 | 345 | 40 |
| 24, 32 | | | 50 |
| 44 | | | 65 |
| 56 | | | 75 |

(Dimensions in mm)

(2) Dimensions for outer box



| L | W | Н |
|-----|-----|-----|
| 415 | 400 | 315 |

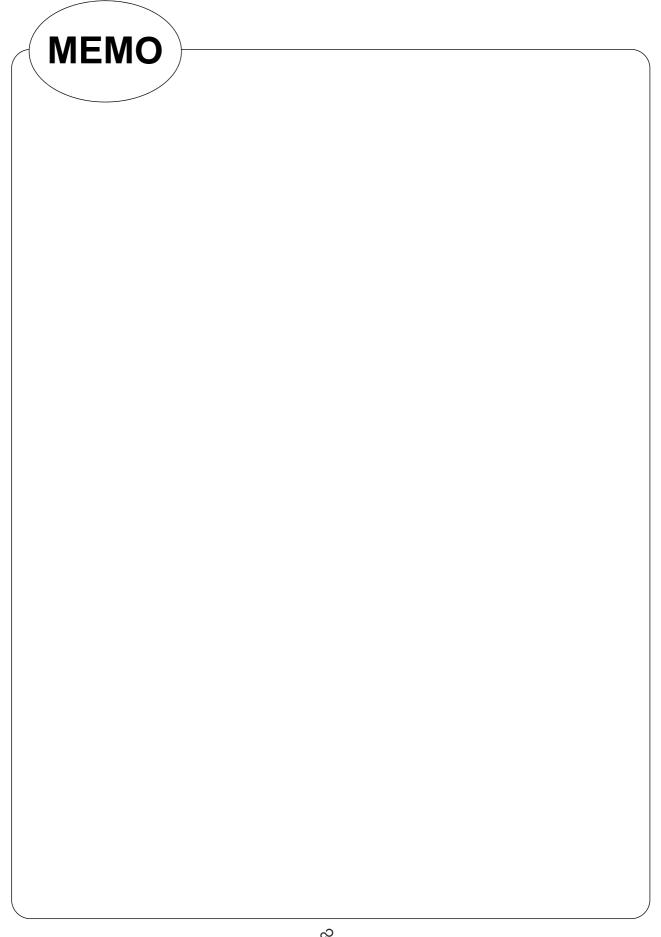
(Dimensions in mm)

■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn on the left side of that page.

| Page | Section | Change Results |
|------|---------------------------|---|
| 1 | ■ FEATURES | Revised the Data retention 10 years (+ 85 °C) →10 years (+ 85 °C), 95 years (+ 55 °C), over 200 years (+ 35 °C) |
| 5 | ■ ABSOLUTE MAXIMUM RANGES | Revised the Storage Temperature $-40 \text{ °C} \rightarrow -55 \text{ °C}$ |
| 10 | ■ POWER ON/OFF SEQUENCE | Deleted the following description: "Because turning the power-on from an intermediate level cause malfunction, when the power is turned on, V _{DD} is re- quired to be started from 0V (see the figure below). " Moved the following description under the table: "If the device does not operate within the specified condi- tions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed. " |
| | ■ FRAM CHARACTERISTICS | Revised the table and Note |





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